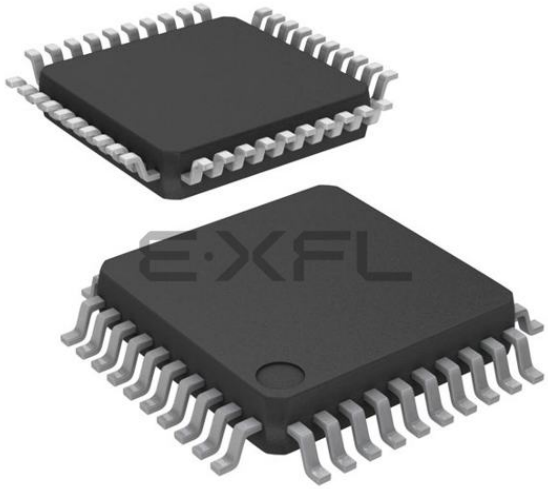
Renesas Electronics America Inc - R5F10RBCAFP#50 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	20
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 4x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10rbcafp-50

1.3.5 64-pin products

- 64-pin plastic WQFN (8 × 8)

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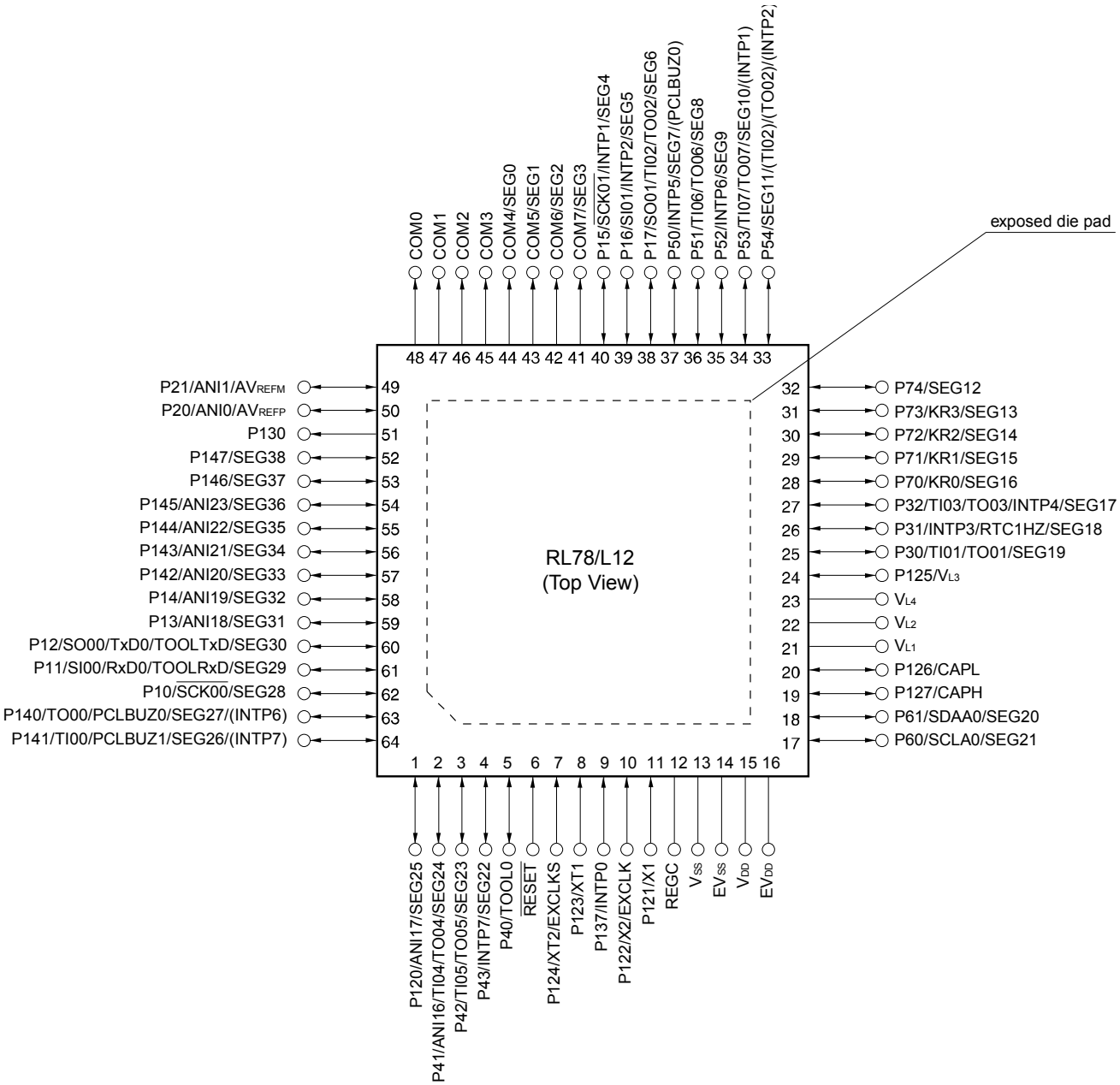


Cautions 1. Make EVSS pin the same potential as VSS pin.

2. Make VDD pin the same potential as EVDD pin.

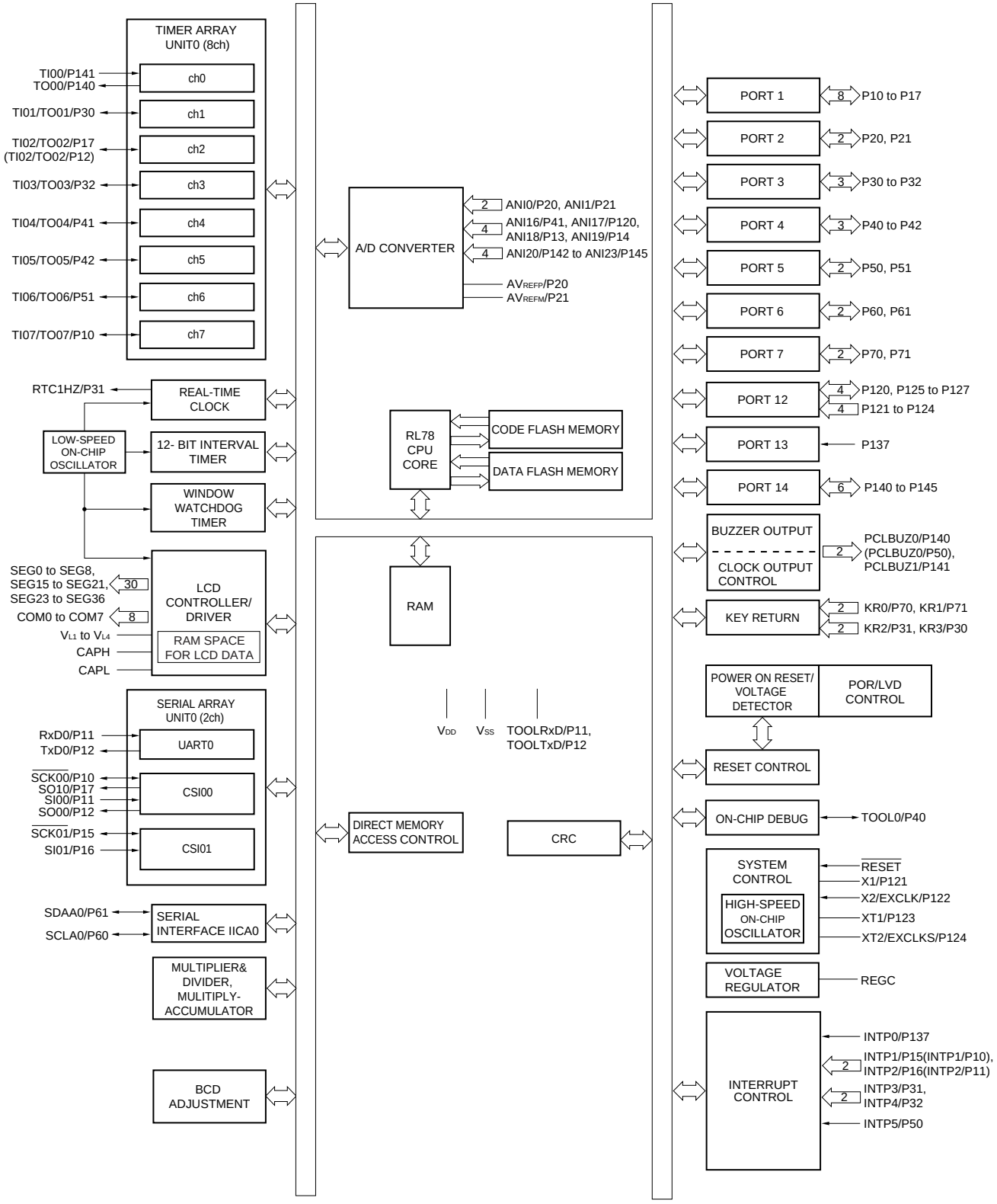
3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification.**

2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD pins and connect the VSS and EVSS pins to separate ground lines.

3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.5.4 52-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) (4/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –10 mA	EV_{DD}–1.5			V
			4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –3.0 mA	EV_{DD}–0.7			V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –2.0 mA	EV_{DD}–0.6			V
			1.8 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –1.5 mA	EV_{DD}–0.5			V
			1.6 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –1.0 mA	EV_{DD}–0.5			V
	V_{OH2}	P20, P21	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OH2} = –100 μA	V_{DD}–0.5			V
Output voltage, low	V_{OL1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 20 mA			1.3	V
			4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
			1.8 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 0.6 mA			0.4	V
			1.6 V ≤ EV_{DD} < 5.5 V, I_{OL1} = 0.3 mA			0.4	V
	V_{OL2}	P20, P21	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60, P61	4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 15.0 mA			2.0	V
			4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 5.0 mA			0.4	V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 3.0 mA			0.4	V
			1.8 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 2.0 mA			0.4	V
			1.6 V ≤ EV_{DD} < 5.5 V, I_{OL3} = 1.0 mA			0.4	V

Caution P10, P12, P15, P17 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) (1/3)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	f_{IH} = 24 MHz Note 3	Basic operation	V_{DD} = 5.0 V		1.5		mA
						V_{DD} = 3.0 V		1.5		mA
					Normal operation	V_{DD} = 5.0 V		3.3	5.0	mA
						V_{DD} = 3.0 V		3.3	5.0	mA
				f_{IH} = 16 MHz Note 3	Normal operation	V_{DD} = 5.0 V		2.5	3.7	mA
						V_{DD} = 3.0 V		2.5	3.7	mA
			LS (low-speed main) mode Note 5	f_{IH} = 8 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.2	1.8	mA
						V_{DD} = 2.0 V		1.2	1.8	mA
			LV (low-voltage main) mode Note 5	f_{IH} = 4 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.2	1.7	mA
						V_{DD} = 2.0 V		1.2	1.7	mA
			HS (high-speed main) mode Note 5	f_{MX} = 20 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		2.8	4.4	mA
						Resonator connection		3.0	4.6	mA
				f_{MX} = 20 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		2.8	4.4	mA
						Resonator connection		3.0	4.6	mA
				f_{MX} = 10 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		1.8	2.6	mA
						Resonator connection		1.8	2.6	mA
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		1.8	2.6	mA
						Resonator connection		1.8	2.6	mA
			LS (low-speed main) mode Note 5	f_{MX} = 8 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		1.1	1.7	mA
						Resonator connection		1.1	1.7	mA
				f_{MX} = 8 MHz Note 2, V_{DD} = 2.0 V	Normal operation	Square wave input		1.1	1.7	mA
						Resonator connection		1.1	1.7	mA
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 4 T_A = –40°C	Normal operation	Square wave input		3.5	4.9	μA
						Resonator connection		3.6	5.0	μA
				f_{SUB} = 32.768 kHz Note 4 T_A = +25°C	Normal operation	Square wave input		3.6	4.9	μA
						Resonator connection		3.7	5.0	μA
				f_{SUB} = 32.768 kHz Note 4 T_A = +50°C	Normal operation	Square wave input		3.7	5.5	μA
						Resonator connection		3.8	5.6	μA
				f_{SUB} = 32.768 kHz Note 4 T_A = +70°C	Normal operation	Square wave input		3.8	6.3	μA
						Resonator connection		3.9	6.4	μA
				f_{SUB} = 32.768 kHz Note 4 T_A = +85°C	Normal operation	Square wave input		4.1	7.7	μA
						Resonator connection		4.2	7.8	μA

(**Notes** and **Remarks** are listed on the next page.)

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	2.7 V ≤ EV_{DD} ≤ 5.5 V		167 Note 1		500 Note 1		1000 Note 1		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		250 Note 1		500 Note 1		1000 Note 1		ns
		1.8 V ≤ EV_{DD} ≤ 5.5 V				500 Note 1		1000 Note 1		ns
		1.6 V ≤ EV_{DD} ≤ 5.5 V						1000 Note 1		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY1}/2 – 12		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		2.7 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY1}/2 – 18		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY1}/2 – 38		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		1.8 V ≤ EV_{DD} ≤ 5.5 V				t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		1.6 V ≤ EV_{DD} ≤ 5.5 V						t_{KCY1}/2 – 100		ns
SIp setup time (to SCKp↑) Note 2	t_{SIK1}	2.7 V ≤ EV_{DD} ≤ 5.5 V		44		110		110		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		75		110		110		ns
		1.8 V ≤ EV_{DD} ≤ 5.5 V				110		110		ns
		1.6 V ≤ EV_{DD} ≤ 5.5 V						220		ns
SIp hold time (from SCKp↑) Note 3	t_{KSI1}	2.4 V ≤ EV_{DD} ≤ 5.5 V		19		19		19		ns
		1.8 V ≤ EV_{DD} ≤ 5.5 V				19		19		
		1.6 V ≤ EV_{DD} ≤ 5.5 V						19		
Delay time from SCKp↓ to SOp output Note 4	t_{KSO1}	C = 30 pF Note 5	2.4 V ≤ EV_{DD} ≤ 5.5 V		25		25		25	ns
			1.8 V ≤ EV_{DD} ≤ 5.5 V				25		25	
			1.6 V ≤ EV_{DD} ≤ 5.5 V						25	

Notes 1. For CSI00, set a cycle of 2/f_{MCK} or longer. For CSI01, set a cycle of 4/f_{MCK} or longer.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

5. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

(**Remarks** are listed on the next page.)

Remarks 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 1)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00, 01))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time[Note 5]	t_{KCY2}	4.0 V ≤ EV_{DD} ≤ 5.5 V	20 MHz < f_{MCK}	8/f_{MCK}						ns
			f_{MCK} ≤ 20 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.7 V ≤ EV_{DD} < 4.0 V	16 MHz < f_{MCK}	8/f_{MCK}						ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		6/f_{MCK} and 500		6/f_{MCK}		6/f_{MCK}		ns
		1.8 V ≤ EV_{DD} < 2.4 V				6/f_{MCK}		6/f_{MCK}		ns
		1.6 V ≤ EV_{DD} < 1.8 V						6/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY2}/2 – 7		t_{KCY2}/2 – 7		t_{KCY2}/2 – 7		ns
		2.7 V ≤ EV_{DD} < 4.0 V		t_{KCY2}/2 – 8		t_{KCY2}/2 – 8		t_{KCY2}/2 – 8		ns
		2.4 V ≤ EV_{DD} < 2.7 V		t_{KCY2}/2 – 18		t_{KCY2}/2 – 18		t_{KCY2}/2 – 18		ns
		1.8 V ≤ EV_{DD} < 2.4 V				t_{KCY2}/2 – 18		t_{KCY2}/2 – 18		ns
		1.6 V ≤ EV_{DD} < 1.8 V						t_{KCY2}/2 – 66		ns
SIp setup time (to SCKp↑)[Note 1]	t_{SIK2}	2.7 V ≤ EV_{DD} ≤ 5.5 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.4 V ≤ EV_{DD} < 2.7 V		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		
		1.8 V ≤ EV_{DD} < 2.4 V				1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.6 V ≤ EV_{DD} < 1.8 V						1/f_{MCK} + 40		ns
SIp hold time (from SCKp↑)[Note 2]	t_{KSI2}	2.4 V ≤ EV_{DD} ≤ 5.5 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.8 V ≤ EV_{DD} < 2.4 V				1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.6 V ≤ EV_{DD} < 1.8 V						1/f_{MCK} + 250		ns

(**Notes**, **Caution,** and **Remarks** are listed on the next page.)

3. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

5. Use it with $EV_{DD} \geq V_b$.

6. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V ≤ EV_{DD} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

7. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (32-pin to 52-pin products)/EV_{DD} tolerance (64-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	20 MHz < f_{MCK} ≤ 24 MHz	12/f_{MCK}						ns
			8 MHz < f_{MCK} ≤ 20 MHz	10/f_{MCK}						ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}				ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	20 MHz < f_{MCK} ≤ 24 MHz	16/f_{MCK}						ns
			16 MHz < f_{MCK} ≤ 20 MHz	14/f_{MCK}						ns
			8 MHz < f_{MCK} ≤ 16 MHz	12/f_{MCK}						ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}				ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V	20 MHz < f_{MCK} ≤ 24 MHz	36/f_{MCK}						ns
			16 MHz < f_{MCK} ≤ 20 MHz	32/f_{MCK}						ns
			8 MHz < f_{MCK} ≤ 16 MHz	26/f_{MCK}						ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		16/f_{MCK}				ns
			f_{MCK} ≤ 4 MHz	10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	4 MHz < f_{MCK} ≤ 8 MHz			16/f_{MCK}				ns
			f_{MCK} ≤ 4 MHz			10/f_{MCK}		10/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		t_{KCY2}/2 – 12		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 – 18		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
		2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2				t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
SIp setup time (to SCKp↑) Note 3	t_{SIK2}	4.0 V ≤ EV_{DD} < 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2				1/f_{MCK} + 30		1/f_{MCK} + 30		ns
SIp hold time (from SCKp↑) Note 4	t_{KSI2}	4.0 V ≤ EV_{DD} < 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2				1/f_{MCK} + 31		1/f_{MCK} + 31		ns

(**Notes**, **Caution** and **Remarks** are listed on the next page.)

3. ELECTRICAL SPECIFICATIONS (G: T_A = -40 to +105°C)

This chapter describes the electrical specifications for the products "G: Industrial applications (T_A = -40 to +105°C)".

Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

2. With products not provided with an EV_{DD} or EV_{SS} pin, replace EV_{DD} with V_{DD}, or replace EV_{SS} with V_{SS}.

3. For derating with T_A = +85 to +105°C, contact our Sales Division or the vender's sales division. Derating means the specified reduction in an operating parameter to improve reliability.

There are following differences between the products "G: Industrial applications (T_A = -40 to +105°C)" and the products “A: Consumer applications, and G: Industrial applications (T_A = -40 to +85°C)”.

Parameter	Application	
	A: Consumer applications, G: Industrial applications (with T_A = -40 to +85°C)	G: Industrial applications
Operating ambient temperature	T_A = -40 to +85°C	T_A = -40 to +105°C
Operating mode Operating voltage range	HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz 2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz	HS (high-speed main) mode only: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz 2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
High-speed on-chip oscillator clock accuracy	1.8 V ≤ V_{DD} ≤ 5.5 V: ±1.0%@ T_A = -20 to +85°C ±1.5%@ T_A = -40 to -20°C 1.6 V ≤ V_{DD} < 1.8 V: ±5.0%@ T_A = -20 to +85°C ±5.5%@ T_A = -40 to -20°C	2.4 V ≤ V_{DD} ≤ 5.5 V: ±2.0%@ T_A = +85 to +105°C ±1.0%@ T_A = -20 to +85°C ±1.5%@ T_A = -40 to -20°C
Serial array unit	UART CSI00: f_{CLK}/2 (supporting 16 Mbps), f_{CLK}/4 CSI01 Simplified I^2C communication	UART CSI00: f_{CLK}/4 CSI01 Simplified I^2C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V (14 levels) Fall detection voltage: 1.63 V to 3.98 V (14 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

Remark The electrical characteristics of the products G: Industrial applications (T_A = -40 to +105°C) are different from those of the products “A: Consumer applications, and G: Industrial applications (only with T_A = -40 to +85°C)”. For details, refer to **3.1** to **3.10**.

Absolute Maximum Ratings (T_A = 25°C) (3/3)

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	I_{OH1}	Per pin	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P130, P140 to P147	−40	mA
		Total of all pins −170 mA	P10 to P14, P40 to P43, P120, P130, P140 to P147	−70	mA
			P15 to P17, P30 to P32, P50 to P54, P70 to P74, P125 to P127	−100	mA
	I_{OH2}	Per pin	P20, P21	−0.5	mA
		Total of all pins		−1	mA
Output current, low	I_{OL1}	Per pin	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P60, P61, P70 to P74, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P10 to P14, P40 to P43, P120, P130, P140 to P147	70	mA
			P15 to P17, P30 to P32, P50 to P54, P60, P61, P70 to P74, P125 to P127	100	mA
	I_{OL2}	Per pin	P20, P21	1	mA
		Total of all pins		2	mA
Operating ambient temperature	T_A	In normal operation mode		−40 to +105	°C
		In flash memory programming mode			
Storage temperature	T_{stg}			−65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

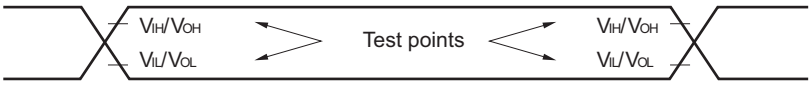
(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) (5/5)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P60, P61, P70 to P74, P120, P125 to P127, P140 to P147	V_I = EV_{DD}				1	μA
	I_{LIH2}	P20, P21, P137, $\overline{\text{RESET}}$	V_I = V_{DD}				1	μA
	I_{LIH3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V_I = V_{DD}	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	I_{LIL1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P60, P61, P70 to P74, P120, P125 to P127, P140 to P147	V_I = EV_{SS}				–1	μA
	I_{LIL2}	P20, P21, P137, $\overline{\text{RESET}}$	V_I = V_{SS}				–1	μA
	I_{LIL3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V_I = V_{SS}	In input port or external clock input			–1	μA
				In resonator connection			–10	μA
On-chip pll-up resistance	R_{U1}	V_I = EV_{SS}	SEGxx port					
			2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V		10	20	100	kΩ
	R_{U2}		Ports other than above (Except for P60, P61, and P130)		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate Note 1				f_{MCK}/12	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		2.0	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

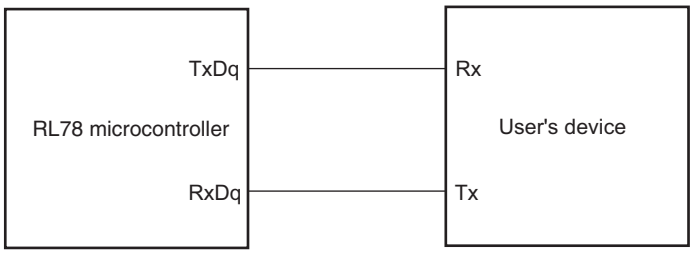
2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)

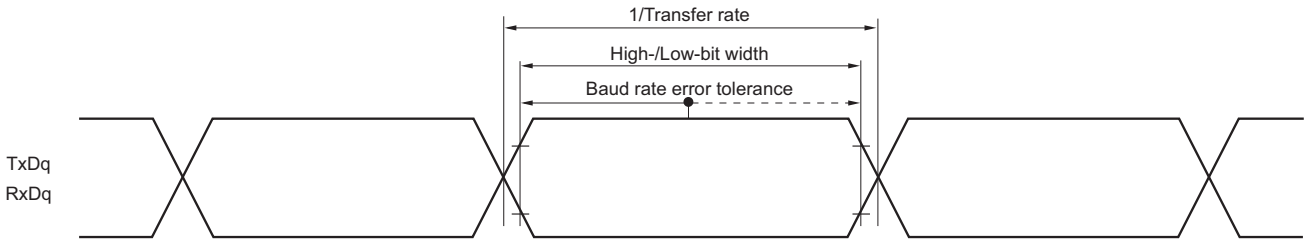
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0), g: PIM and POM number (g = 1)

2. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(4) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions			HS (high-speed main) Mode		Unit
					MIN.	MAX.	
Transfer rate		Reception	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			f_{MCK}/12 Note 1	bps
				Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		2.0	Mbps
			2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V			f_{MCK}/12 Note 1	bps
				Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		2.0	Mbps
			2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			f_{MCK}/12 Note 1	bps
				Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		2.0	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (32- to 52-pin products)/EV_{DD} tolerance (64-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

2. q: UART number (q = 0), g: PIM and POM number (g = 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01)

(4) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions			HS (high-speed main) Mode		Unit
					MIN.	MAX.	
Transfer rate		Transmission	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			**Note 1**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.0 Note 2	Mbps
			2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V			**Note 3**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 4	Mbps
			2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			**Note 5**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 6	Mbps

Notes 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

2. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

3. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

(2) I^2C fast mode

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode: f_{CLK} ≥ 3.5 MHz	2.7 V ≤ EV_{DD} ≤ 5.5 V	0	400	kHz
			2.4 V ≤ EV_{DD} ≤ 5.5 V	0	400	
Setup time of restart condition	$t_{SU:STA}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.6		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		0.6		
Hold time Note 1	$t_{HD:STA}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.6		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		0.6		
Hold time when SCLA0 = “L”	t_{LOW}	2.7 V ≤ EV_{DD} ≤ 5.5 V		1.3		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		1.3		
Hold time when SCLA0 = “H”	t_{HIGH}	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.6		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		0.6		
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		100		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		100		
Data hold time (transmission) Note 2	$t_{HD:DAT}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0	0.9	μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		0	0.9	
Setup time of stop condition	$t_{SU:STO}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.6		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		0.6		
Bus-free time	t_{BUF}	2.7 V ≤ EV_{DD} ≤ 5.5 V		1.3		μs
		2.4 V ≤ EV_{DD} ≤ 5.5 V		1.3		

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the $\overline{ACK}$ (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

3.6.2 Temperature sensor/internal reference voltage characteristics

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V, HS (high-speed main) mode)

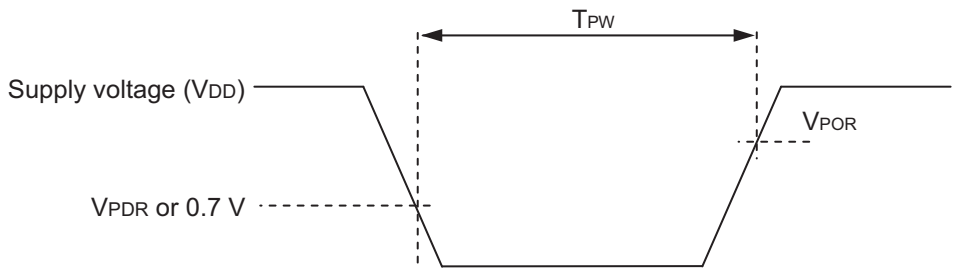
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, T_A = +25°C		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor that depends on the temperature		–3.6		mV/°C
Operation stabilization wait time	t_{AMP}		5			μs

3.6.3 POR circuit characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.45	1.51	1.57	V
	V_{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width	T_{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.7 LCD Characteristics

3.7.1 Resistance division method

(1) Static display mode

(T_A = –40 to +105°C, V_{L4} (MIN.) ≤ V_{DD}[Note] ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.0		V_{DD}	V

Note Must be 2.4 V or higher.

(2) 1/2 bias method, 1/4 bias method

(T_A = –40 to +105°C, V_{L4} (MIN.) ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.7		V_{DD}	V

(3) 1/3 bias method

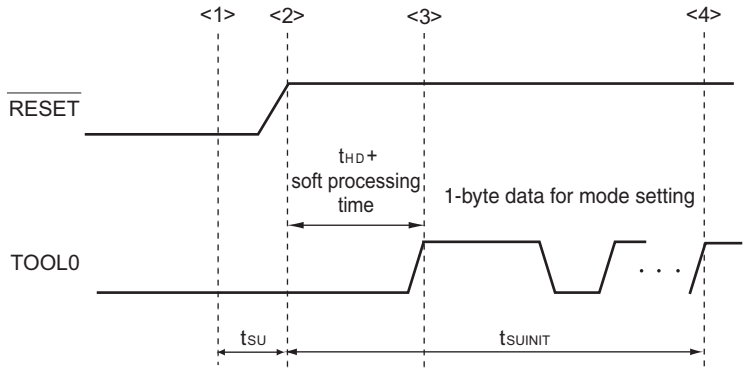
(T_A = –40 to +105°C, V_{L4} (MIN.) ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.5		V_{DD}	V

3.11 Timing Specifications for Switching Flash Memory Programming Modes

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUINIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

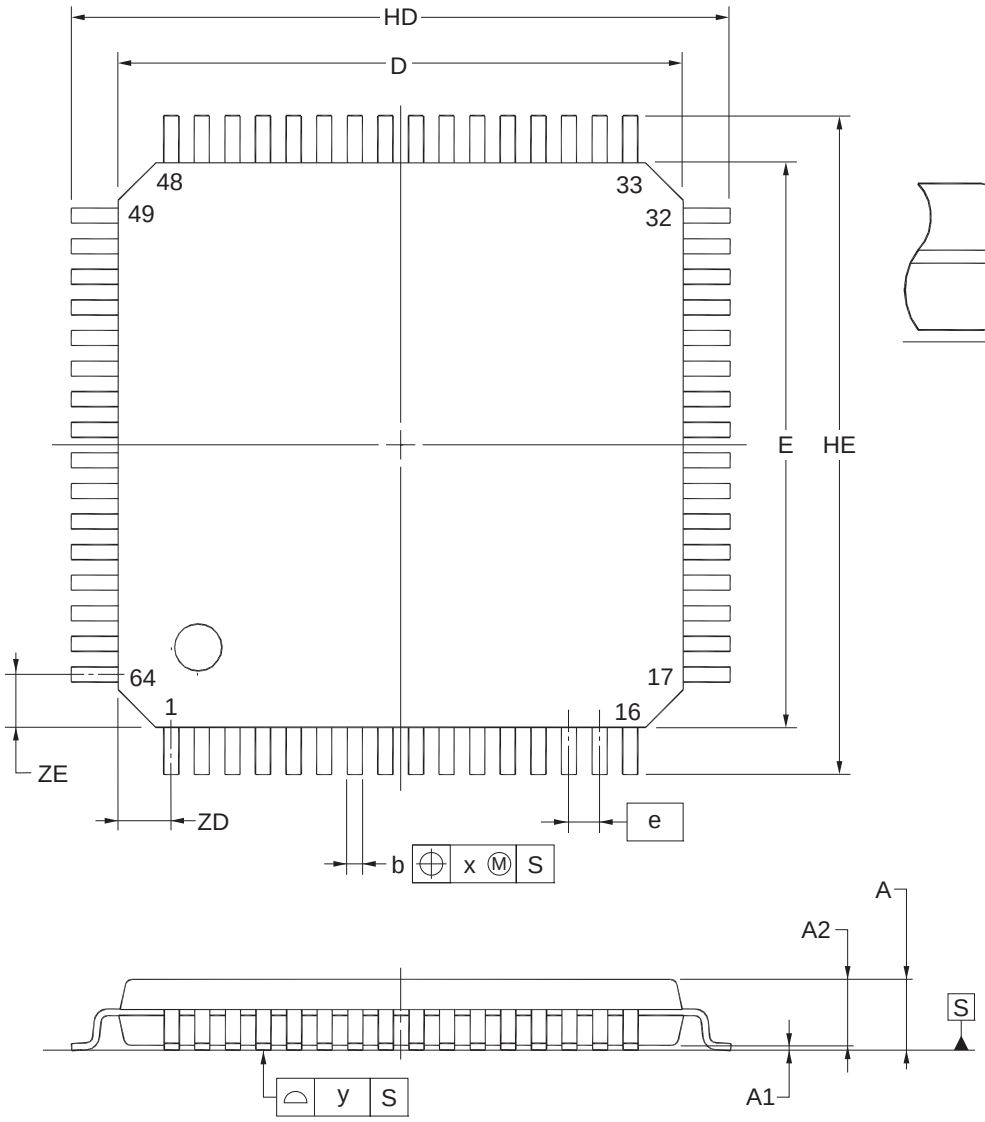
t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

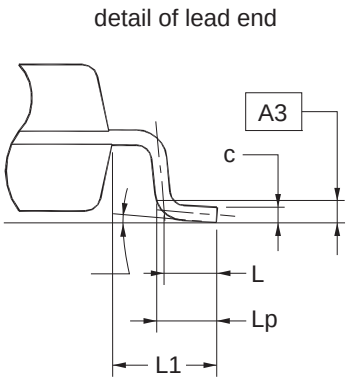
t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

4.5 64-pin Products

R5F10RLAAFA, R5F10RLCAFA
R5F10RLAGFA, R5F10RLCGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51





(UNIT:mm)

ITEM	DIMENSIONS
D	12.00±0.20
E	12.00±0.20
HD	14.00±0.20
HE	14.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	$0.32^{+0.08}_{0.07}$
c	$0.145^{+0.055}_{0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
	$3^{\circ}{}^{+5^{\circ}}_{3^{\circ}}$
e	0.65
x	0.13
y	0.10
ZD	1.125
ZE	1.125

NOTE
Each lead centerline is located within 0.13 mm of its true position at maximum material condition.